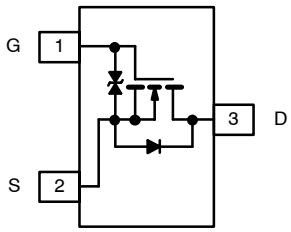
N-Channel 1.8-V (G-S) MOSFET

PRODUCT SUMMARY		
V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (mA)
20	0.70 @ V_{GS} = 4.5 V	600
	0.85 @ V_{GS} = 2.5 V	500
	1.25 @ V_{GS} = 1.8 V	350

SC-75A or SC-89



Top View

ORDERING INFORMATION		
Part Number	Package	Marking Code
Si1012R-T1 Si1012R-T1—E3 (Lead (Pb)-Free)	SC–75A (SOT-416)	C
Si1012X-T1 Si1012X-T1—E3 (Lead (Pb)-Free)	SC-89 (SOT-490)	A

FEATURES

- TrenchFET® Power MOSFET: 1.8-V Rated
- Gate-Source ESD Protected: 2000 V
- High-Side Switching
- Low On-Resistance: 0.7 Ω
- Low Threshold: 0.8 V (typ)
- Fast Switching Speed: 10 ns

Pb-free Available

BENEFITS

- Ease in Driving Switches
- Low Offset (Error) Voltage
- Low-Voltage Operation
- High-Speed Circuits
- Low Battery Voltage Operation

APPLICATIONS

- Drivers: Relays, Solenoids, Lamps, Hammers, Displays, Memories
- Battery Operated Systems
- Power Supply Converter Circuits
- Load/Power Switching Cell Phones, Pagers

ABSOLUTE MAXIMUM RATINGS (T_A = 25°C UNLESS OTHERWISE NOTED)					
Parameter		Symbol	5 secs	Steady State	Unit
Drain-Source Voltage		V_{DS}	20		V
Gate-Source Voltage		V_{GS}	±6		
Continuous Drain Current (T_J = 150°C)[b]	T_A = 25°C	I_D	600	500	mA
	T_A = 85°C		400	350	
Pulsed Drain Current[a]		I_{DM}	1000		
Continuous Source Current (diode conduction)[b]		I_S	275	250	
Maximum Power Dissipation[b] for SC-75	T_A = 25°C	P_D	175	150	mW
	T_A = 85°C		90	80	
Maximum Power Dissipation[b] for SC-89	T_A = 25°C		275	250	
	T_A = 85°C		160	140	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	–55 to 150		°C
Gate-Source ESD Rating (HBM, Method 3015)		ESD	2000		V

Notes
d. Pulse width limited by maximum junction temperature.
e. Surface Mounted on FR4 Board.

SPECIFICATIONS (T_A = 25°C UNLESS OTHERWISE NOTED)

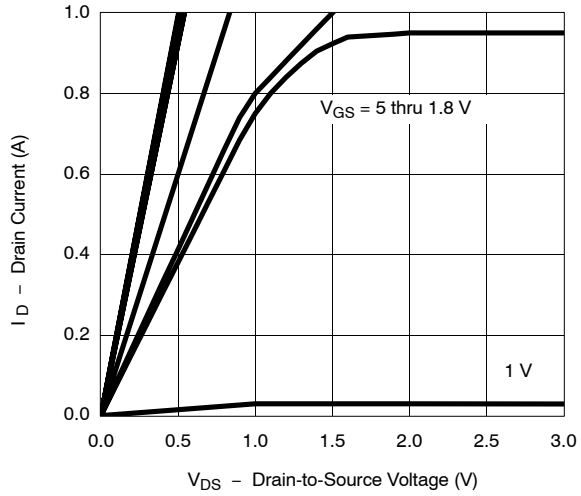
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 μA	0.45		0.9	V
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ±4.5 V		±0.5	±1.0	μA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 20 V, V_{GS} = 0 V		0.3	100	nA
		V_{DS} = 20 V, V_{GS} = 0 V, T_J = 85°C			5	μA
On-State Drain Current[a]	$I_{D(on)}$	V_{DS} = 5 V, V_{GS} = 4.5 V	700			mA
Drain-Source On-State Resistance[a]	$r_{DS(on)}$	V_{GS} = 4.5 V, I_D = 600 mA		0.41	0.70	Ω
		V_{GS} = 2.5 V, I_D = 500 m A		0.53	0.85	
		V_{GS} = 1.8 V, I_D = 350 m A		0.70	1.25	
Forward Transconductance[a]	g_{fs}	V_{DS} = 10 V, I_D = 400 mA		1.0		S
Diode Forward Voltage[a]	V_{SD}	I_S = 150 mA, V_{GS} = 0 V		0.8	1.2	V
Dynamic[b]						
Total Gate Charge	Q_g	V_{DS} = 10 V, V_{GS} = 4.5 V, I_D = 250 mA		750		pC
Gate-Source Charge	Q_{gs}			75		
Gate-Drain Charge	Q_{gd}			225		
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = 10 V, R_L = 47 Ω I_D ≅ 200 mA, V_{GEN} = 4.5 V, R_G = 10 Ω		5		ns
Rise Time	t_r			5		
Turn-Off Delay Time	$t_{d(off)}$			25		
Fall Time	t_f			11		

Notes
a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.
b. Guaranteed by design, not subject to production testing.

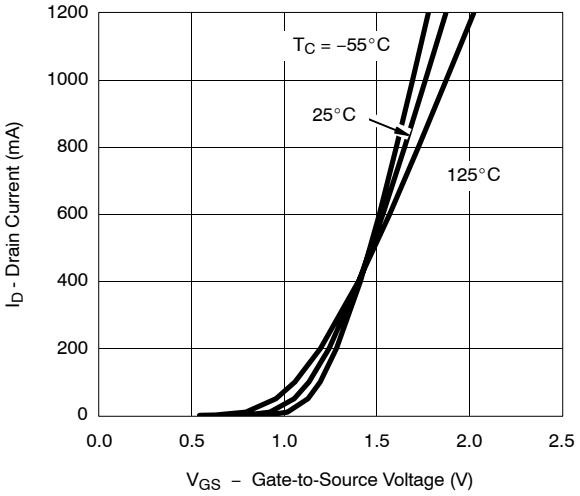
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS (T_A = 25°C UNLESS NOTED)

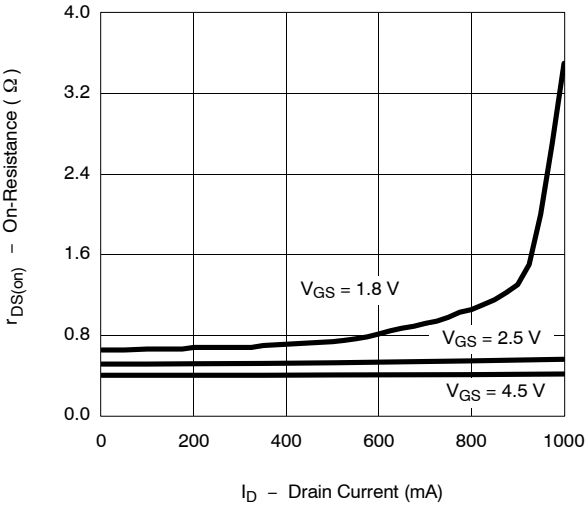
Output Characteristics



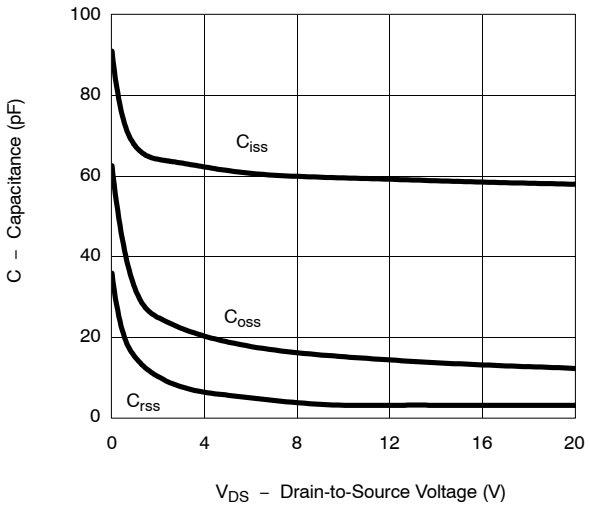
Transfer Characteristics



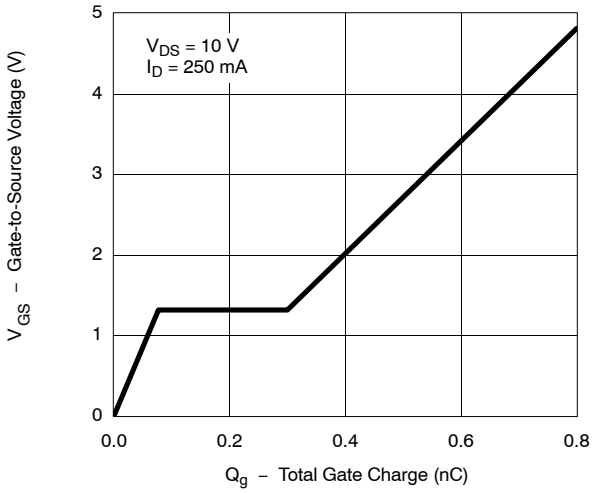
On-Resistance vs. Drain Current



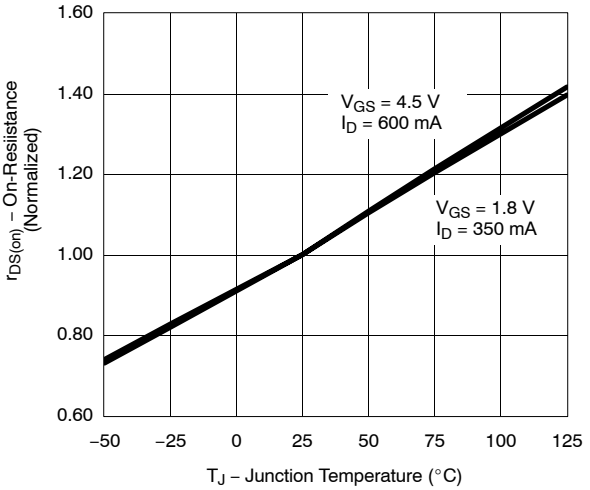
Capacitance



Gate Charge

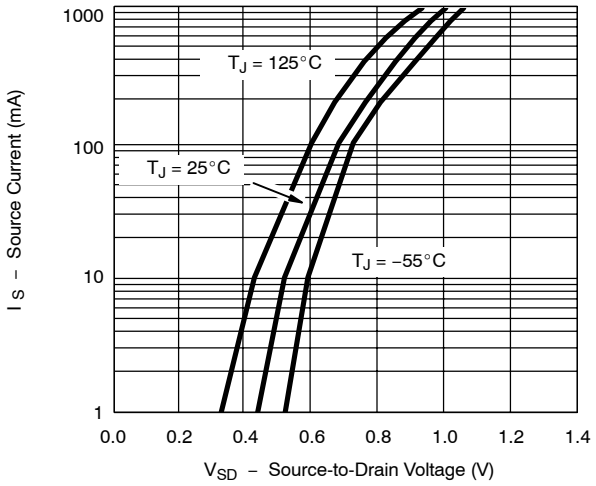


On-Resistance vs. Junction Temperature

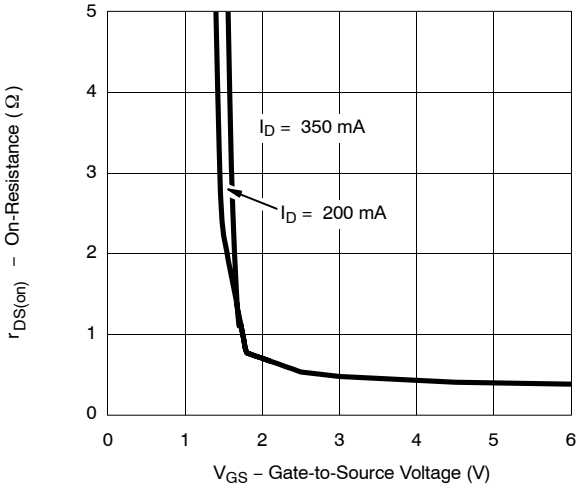


TYPICAL CHARACTERISTICS (T_A = 25°C UNLESS NOTED)

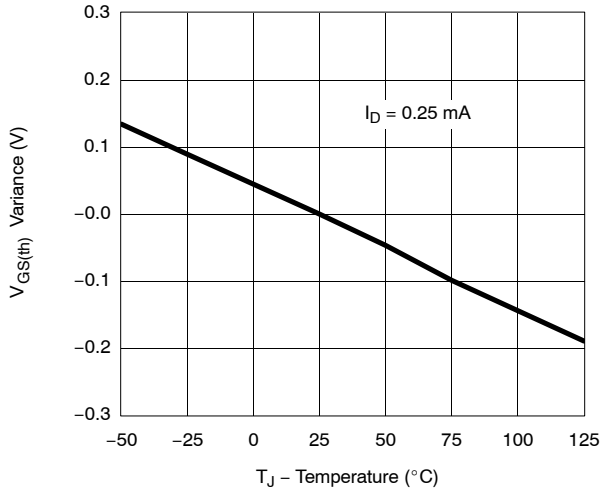
Source-Drain Diode Forward Voltage



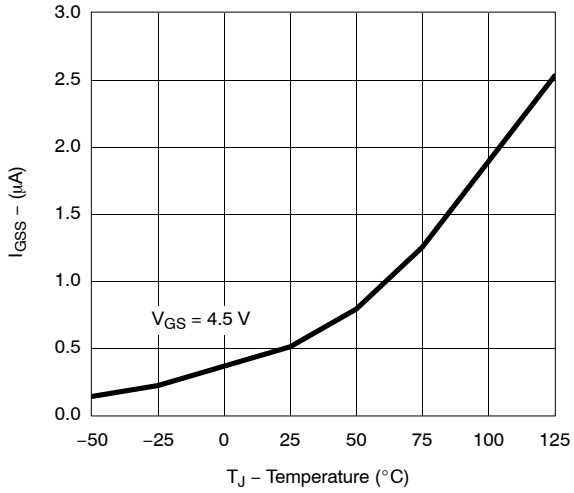
On-Resistance vs. Gate-to-Source Voltage



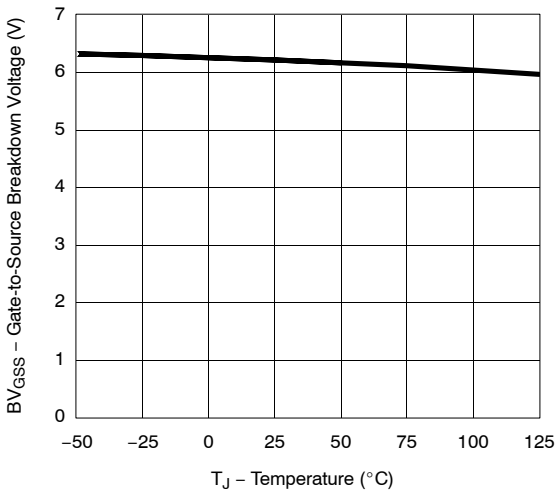
Threshold Voltage Variance vs. Temperature



I_{GSS} vs. Temperature

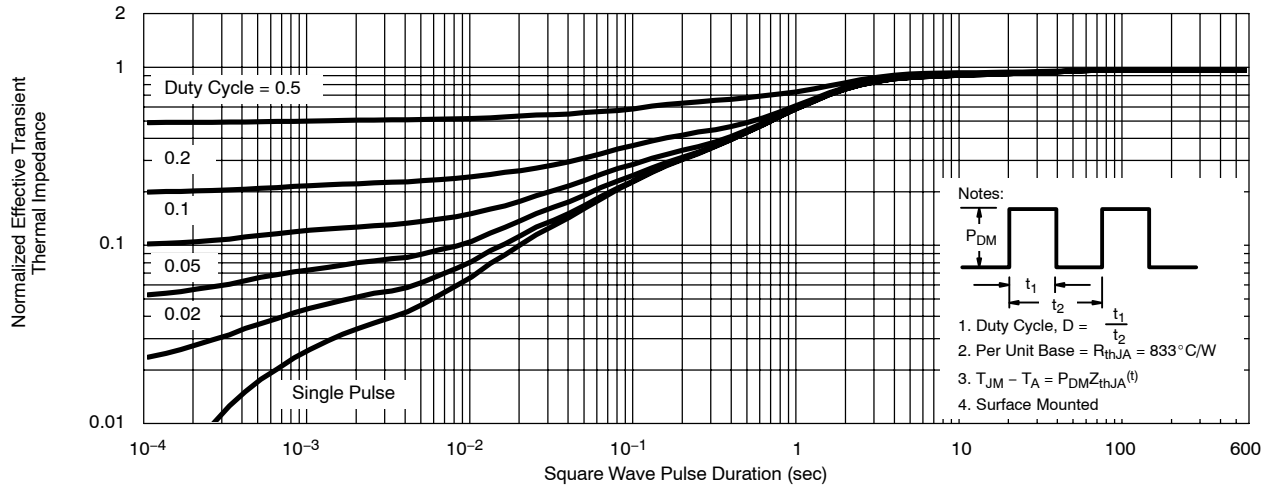


BV_{GSS} vs. Temperature

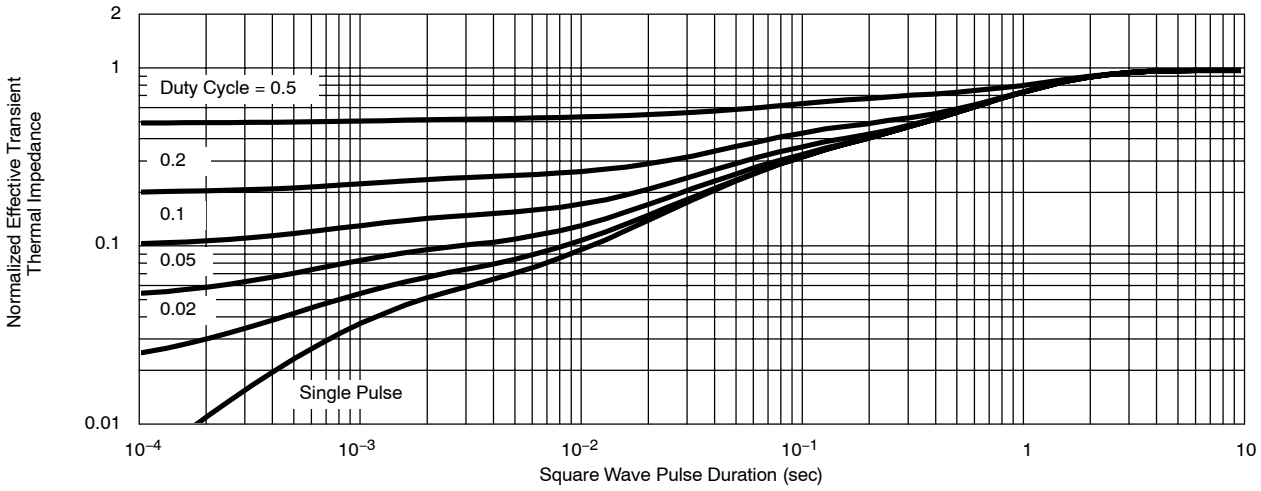


TYPICAL CHARACTERISTICS (T_A = 25°C UNLESS NOTED)

Normalized Thermal Transient Impedance, Junction-to-Ambient (SC-75A)



Normalized Thermal Transient Impedance, Junction-to-Foot



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